

IN THE CLAIMS:

Please amend claims 57, 63, 69, 75, 81 and 87 as follows:

1-56. (Canceled)

57. (Currently Amended) A semiconductor device comprising:

- a substrate having a metal surface;
- a base insulating film formed on the substrate having the metal surface;
- a switching thin film transistor and a current controlling thin film transistor, both formed on the base insulating film in a pixel unit, wherein each of the thin film transistors comprises a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;
- an interlayer insulating film formed over the switching thin film transistor and the current controlling thin film transistor, wherein a portion of the interlayer insulating film is removed so as to expose a portion of the base insulating film;
- a metal wiring formed on the exposed portion of the base insulating film; and
- a storage capacitor comprising a portion of the substrate having the metal surface, the exposed portion of the base insulating film, and the metal wiring.

58. (Original) A semiconductor device according to claim 57, wherein the metal surface comprises a stainless steel.

59. (Original) A semiconductor device according to claim 57, wherein the switching thin film transistor is a p-channel thin film transistor.

60. (Original) A semiconductor device according to claim 57, wherein the current controlling thin film transistor is an n-channel thin film transistor.

61. (Original) A semiconductor device according to claim 57, wherein the semiconductor device is a light-emitting device.

62. (Original) A semiconductor device according to claim 57, wherein the semiconductor device is one selected from the group consisting of a portable telephone, a video camera, a digital

camera, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

63. (Currently Amended) A semiconductor device comprising:

- a substrate having a metal surface;
- a base insulating film formed on the substrate having the metal surface;
- a switching thin film transistor and a current controlling thin film transistor, both formed on the base insulating film in a pixel unit, wherein each of the thin film transistors comprises a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;
- an interlayer insulating film formed over the switching thin film transistor and the current controlling thin film transistor, wherein a portion of the interlayer insulating film is removed so as to expose a portion of the base insulating film;
- a metal wiring formed on the exposed portion of the base insulating film and electrically connected to the gate electrode of the current controlling thin film transistor; and
- a storage capacitor comprising a portion of the substrate having the metal surface, the exposed portion of the base insulating film, and the metal wiring.

64. (Original) A semiconductor device according to claim 63, wherein the metal surface comprises a stainless steel.

65. (Original) A semiconductor device according to claim 63, wherein the switching thin film transistor is a p-channel thin film transistor.

66. (Original) A semiconductor device according to claim 63, wherein the current controlling thin film transistor is an n-channel thin film transistor.

67. (Original) A semiconductor device according to claim 63, wherein the semiconductor device is a light-emitting device.

68. (Original) A semiconductor device according to claim 63, wherein the semiconductor device is one selected from the group consisting of a portable telephone, a video camera, a digital

camera, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

69. (Currently Amended) A semiconductor device comprising:

- a substrate having a metal surface;
- a base insulating film formed on the substrate having the metal surface;
- a switching thin film transistor and a current controlling thin film transistor, both formed on the base insulating film in a pixel unit, wherein each of the thin film transistors comprises a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;
- an interlayer insulating film formed over the switching thin film transistor and the current controlling thin film transistor, wherein a portion of the interlayer insulating film is removed so as to expose a portion of the base insulating film;
- a metal wiring formed on the exposed portion of the base insulating film and electrically connected to the semiconductor layer of the switching thin film transistor; and
- a storage capacitor comprising a portion of the substrate having the metal surface, the exposed portion of the base insulating film, and the metal wiring.

70. (Original) A semiconductor device according to claim 69, wherein the metal surface comprises a stainless steel.

71. (Original) A semiconductor device according to claim 69, wherein the switching thin film transistor is a p-channel thin film transistor.

72. (Original) A semiconductor device according to claim 69, wherein the current controlling thin film transistor is an n-channel thin film transistor.

73. (Original) A semiconductor device according to claim 69, wherein the semiconductor device is a light-emitting device.

74. (Original) A semiconductor device according to claim 69, wherein the semiconductor device is one selected from the group consisting of a portable telephone, a video camera, a digital

camera, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

75. (Currently Amended) A semiconductor device comprising:

- a metal substrate;
- a base insulating film formed on the metal substrate;
- a switching thin film transistor and a current controlling thin film transistor, both formed on the base insulating film in a pixel unit, wherein each of the thin film transistors comprises a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;
- an interlayer insulating film formed over the switching thin film transistor and the current controlling thin film transistor, wherein a portion of the interlayer insulating film is removed so as to expose a portion of the base insulating film;
- a metal wiring formed on the exposed portion of the base insulating film; and
- a storage capacitor comprising a portion of the metal substrate, the exposed portion of the base insulating film, and the metal wiring.

76. (Original) A semiconductor device according to claim 75, wherein the metal substrate comprises a stainless steel substrate.

77. (Original) A semiconductor device according to claim 75, wherein the switching thin film transistor is a p-channel thin film transistor.

78. (Original) A semiconductor device according to claim 75, wherein the current controlling thin film transistor is an n-channel thin film transistor.

79. (Original) A semiconductor device according to claim 75, wherein the semiconductor device is a light-emitting device.

80. (Original) A semiconductor device according to claim 75, wherein the semiconductor device is one selected from the group consisting of a portable telephone, a video camera, a digital

camera, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

81. (Currently Amended) A semiconductor device comprising:

a metal substrate;

a base insulating film formed on the metal substrate;

a switching thin film transistor and a current controlling thin film transistor, both formed on the base insulating film in a pixel unit, wherein each of the thin film transistors comprises a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;

an interlayer insulating film formed over the switching thin film transistor and the current controlling thin film transistor, wherein a portion of the interlayer insulating film is removed so as to expose a portion of the base insulating film;

a metal wiring formed on the exposed portion of the base insulating film and electrically connected to the gate electrode of the current controlling thin film transistor; and

a storage capacitor comprising a portion of the metal substrate, the exposed portion of the base insulating film, and the metal wiring.

82. (Original) A semiconductor device according to claim 81, wherein the metal substrate comprises a stainless steel substrate.

83. (Original) A semiconductor device according to claim 81, wherein the switching thin film transistor is a p-channel thin film transistor.

84. (Original) A semiconductor device according to claim 81, wherein the current controlling thin film transistor is an n-channel thin film transistor.

85. (Original) A semiconductor device according to claim 81, wherein the semiconductor device is a light-emitting device.

86. (Original) A semiconductor device according to claim 81, wherein the semiconductor device is one selected from the group consisting of a portable telephone, a video camera, a digital

camera, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.

87. (Currently Amended) A semiconductor device comprising:

a metal substrate;

a base insulating film formed on the metal substrate;

a switching thin film transistor and a current controlling thin film transistor, both formed on the base insulating film in a pixel unit, wherein each of the thin film transistors comprises a semiconductor layer and a gate electrode with a gate insulating film interposed therebetween;

an interlayer insulating film formed over the switching thin film transistor and the current controlling thin film transistor, wherein a portion of the interlayer insulating film is removed so as to expose a portion of the base insulating film;

a metal wiring formed on the exposed portion of the base insulating film and electrically connected to the semiconductor layer of the switching thin film transistor; and

a storage capacitor comprising a portion of the metal substrate, the exposed portion of the base insulating film, and the metal wiring.

88. (Original) A semiconductor device according to claim 87, wherein the metal substrate comprises a stainless steel substrate.

89. (Original) A semiconductor device according to claim 87, wherein the switching thin film transistor is a p-channel thin film transistor.

90. (Original) A semiconductor device according to claim 87, wherein the current controlling thin film transistor is an n-channel thin film transistor.

91. (Original) A semiconductor device according to claim 87, wherein the semiconductor device is a light-emitting device.

92. (Original) A semiconductor device according to claim 87, wherein the semiconductor device is one selected from the group consisting of a portable telephone, a video camera, a digital

camera, a goggle type display, a personal computer, a DVD player, an electronic book, and a portable information terminal.